4-Bit Dual-Supply Inverting Level Translator

The NLSV4T240E is a 4-bit configurable dual-supply voltage level translator. The input A_n and output B_n ports are designed to track two different power supply rails, V_{CCA} and V_{CCB} respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input A_n to the output B_n port.

The NLSV4T240E is similar to the NLSV4T240; however, it has enhanced power-off characteristics.

Features

- Wide V_{CCA} and V_{CCB} Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V_{CCA} and V_{CCB} Sequencing
- Outputs at 3-State until Active V_{CC} is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V_{CCB} at GND
- Ultra-Small Packaging: 1.7 mm x 2.0 mm UQFN12
- This is a Pb-Free Device

Typical Applications

• Mobile Phones, PDAs, Other Portable Devices

Important Information

• ESD Protection for All Pins:

HBM (Human Body Model) > 6000 V MM (Machine Model) > 300 V



ON Semiconductor®

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MARKING DIAGRAMS



UQFN12 MU SUFFIX CASE 523AE



AE = Specific Device Code

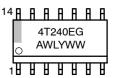
I = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NLSV4T240EMUTAG	UQFN12 (Pb-Free)	3000/Tape & Reel
NLSV4T240EDR2G	SO-14 (Pb-Free)	2500/Tape & Reel
NLSV4T240EDTR2G	TSSOP14 (Pb-Free)	2500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

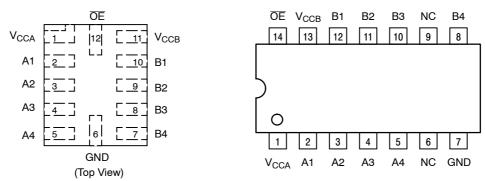


Figure 1. Pin Assignments

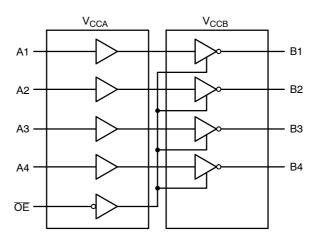


Figure 2. Logic Diagram

PIN ASSIGNMENT

Pin	Function
V _{CCA}	Input Port DC Power Supply
V _{CCB}	Output Port DC Power Supply
GND	Ground
A _n	Input Port
B _n	Output Port
ŌĒ	Output Enable

TRUTH TABLE

In	Outputs	
ŌĒ	A _n	B _n
L	L	Н
L	Н	L
Н	Х	3-State

MAXIMUM RATINGS

Symbol	Rating		Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage		-0.5 to +5.5		V
VI	DC Input Voltage	A _n	-0.5 to +5.5		V
V _C	Control Input	OE	−0.5 to +5.5		V
V _O	DC Output Voltage (Power Down)	B _n	-0.5 to +5.5	V _{CCA} = V _{CCB} = 0	V
	(Active Mode)	B _n	-0.5 to +5.5		V
	(Tri-State Mode)	B _n	-0.5 to +5.5		V
l _{IK}	DC Input Diode Current		-20	V _I < GND	mA
lok	DC Output Diode Current		-50	V _O < GND	mA
I _O	DC Output Source/Sink Current		±50		mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin		±100		mA
I _{GND}	DC Ground Current per Ground Pin		±100		mA
T _{STG}	Storage Temperature		−65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CCA} , V _{CCB}	Positive DC Supply Voltage	0.9	4.5	٧	
VI	Bus Input Voltage		GND	4.5	٧
V _C	Control Input	ŌĒ	GND	4.5	V
V _{IO}	Bus Output Voltage (Power Down Mode)	B _n	GND	4.5	V
	(Active Mode)	B _n	GND	V _{CCB}	V
	(Tri-State Mode)	B _n	GND	4.5	V
T_A	Operating Temperature Range		-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V_{I} , from 30% to 70% of V_{CC} ; V_{CC} = 3.3 V \pm 0.3 V		0	10	nS

DC ELECTRICAL CHARACTERISTICS

					-40°C to	o +85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit
V _{IH}	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.7	_	V
	(An, \overline{OE})		2.7 – 3.6		2.0	-	
			2.3 – 2.7		1.7	-	
			1.4 – 2.3		0.75 * V _{CCA}	-	
			0.9 – 1.4	1	0.9 * V _{CCA}	-	
V _{IL}	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	0.8	V
	(An, \overline{OE})		2.7 – 3.6	1	=	0.8	
			2.3 – 2.7	1	=	0.7	
			1.4 – 2.3	1	=	0.35 * V _{CCA}	
			0.9 – 1.4		_	0.1 * V _{CCA}	

DC ELECTRICAL CHARACTERISTICS

					−40°C to	+85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit
V _{OH}	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	V _{CCB} - 0.2	-	V
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V _{CCB}	-	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	-	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1.25	-	
			2.3	2.3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	-	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IL}$	0.9 – 4.5	0.9 – 4.5	-	0.2	V
		$I_{OL} = 0.5 \text{ mA}; V_I = V_{IH}$	1.1	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	-	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	
		I _{OL} = 12 mA; V _I = V _{IL}	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		I _{OL} = 18 mA; V _I = V _{IL}	2.3	2.3	-	0.6	
			3.0	3.0	-	0.4	
		I _{OL} = 24 mA; V _I = V _{IL}	3.0	3.0	-	0.55	
I _I	Input Leakage Current	V _I = V _{CCA} or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μΑ
I _{OFF}	Power-Off Leakage Current	<u>OE</u> = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μΑ
I _{CCA}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μА
CCA + ICCB	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μА
ΔI_{CCA}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μΑ
ΔI_{CCB}	Increase in I_{CC} per Input Voltage, Other Inputs at V_{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μА
I _{OZ}	I/O Tri-State Output Leakage	V _O = 0 V	4.5	4.5	-	1.0	μА
	Current ($T_A = 25^{\circ}C$, $\overline{OE} = V_{CCA}$)	V _O = 4.5 V	4.5	4.5	-	10	
		V _O = 0 to 4.5 V	2.5	3.5	-	105	1
			3.0	3.75	-	110	1
			3.3	3.0	-	75	1
			3.75	1.5	_	10	1

TOTAL STATIC POWER CONSUMPTION (I_{CCA} + I_{CCB})

	-40°C to +85°C										
					V _{CCI}	_B (V)					
	4.	.5	3.	.3	2.	.8	1.	8	0.	9	
V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

NOTE: Connect ground before applying supply voltage V_{CCA} or V_{CCB}. This device is designed with the feature that the power–up sequence of V_{CCA} and V_{CCB} will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

				-40°C to +85°C									
							V _{CC}	_B (V)					
			4.	.5	3	.3	2.8		1	1.8 1		5	
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation	4.5		3.0		3.2		3.4		3.7		4.0	nS
t _{PHL} (Note 1)	Delay,	3.6		3.3		3.5		3.7		4.0		4.3	
(Note 1)	A _n to B _n	2.8		3.5		3.7		3.9		4.2		4.5	
		1.8		3.8		4.0		4.2		4.5		4.8	
		1.5		4.1		4.3		4.5		4.8		5.0	
t _{PZH} ,	Output	4.5		4.4		4.8		5.2		5.7		6.2	nS
t _{PZL}	Enable,	3.3		4.7		5.1		5.5		6.0		6.5	
(Note 1)	OE to B _n	2.8		4.9		5.3		5.7		6.2		6.7	1
		1.8		5.2		5.6		6.0		6.5		7.0	
		1.5		5.5		5.9		6.3		6.8		7.3	
t _{PHZ} ,	Output	4.5		4.4		4.8		5.2		5.7		6.2	nS
t _{PLZ}	Disable,	3.3		4.7		5.1		5.5		6.0		6.5	
(Note 1)	OE to B _n	2.8		4.9		5.3		5.7		6.2		6.7	
		1.8		5.2		5.6		6.0		6.5		7.0	
		1.5		5.5		5.9		6.3		6.8		7.3	
t _{OSHL} ,	Output Skew,	4.1		0.15		0.15		0.15		0.15		0.15	nS
toslh		3.6		0.15		0.15		0.15		0.15		0.15	
(Note 1)		2.8		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

^{1.} Propagation delays defined per Figures 3 and 4.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C _{IN}	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C _{I/O}	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF

Typical values are at T_A = +25°C.
 C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC(operating)} ≅ C_{PD} x V_{CC} x f_{IN} x N_{SW} where I_{CC} = I_{CCA} + I_{CCB} and N_{SW} = total number of outputs switching.

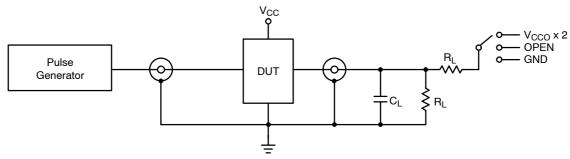


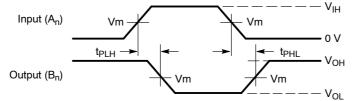
Figure 3. AC (Propagation Delay) Test Circuit

Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PLZ} , t _{PZL}	V _{CCO} x 2
t _{PHZ} , t _{PZH}	GND

 C_L = 15 pF or equivalent (includes probe and jig capacitance)

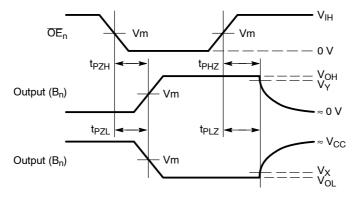
 $R_L = 2 k\Omega$ or equivalent

 Z_{OUT} of pulse generator = 50 Ω



Waveform 1 - Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



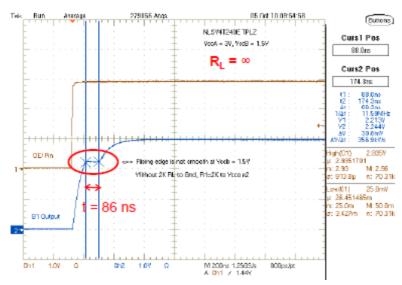
Waveform 2 - Output Enable and Disable Times

 t_{R} = t_{F} = 2.0 ns, 10% to 90%; f = 1 MHz; t_{W} = 500 ns

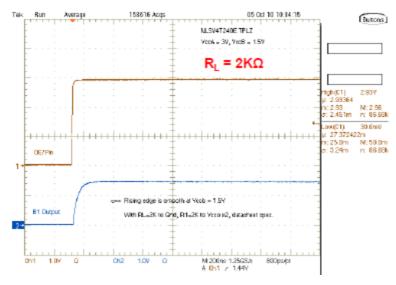
Figure 4. AC (Propagation Delay) Test Circuit Waveforms

	V _{CC}									
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V					
V _{mA}	V _{CCA} /2									
V _{mB}	V _{CCB} /2									
V _X	V _{OL} x 0.1									
V _Y	V _{OH} x 0.9									

APPLICATIONS INFORMATION



(C_L = 50 pF, R_L = 2 k Ω , R_{pull-up} = 50 k Ω , test circuit shown in Figure 3) **Figure 5. Typical Tri–State Output**



(CL = 50 pF, RL = ∞ , $R_{Pull-up}$ = 2 k $\Omega,$ test circuit shown in Figure 3)

Figure 6. Typical Tri-State Output

Typical tri–state output waveforms of the NLSX4T240E are shown in Figures 5 and 6. The shape of the output waveform during a tri–state condition corresponding to the disable time (t_{PHZ} , t_{pLZ}) depends on the configuration of the pull–up circuit. Figure 5 shows a smooth monotonically increasing exponentially waveform because a 2 k Ω resistance is connected between the output and ground.

Figure 6 shows that the output may have a 'shelf' or a short duration where the slope of the waveform is equal to zero if no load resistance is connected to ground. The NLSX4T240E was created from the NLSX4T240 to minimize the 'shelf' of the waveform during the disable time.

UQFN12 1.7x2.0, 0.4P CASE 523AE-01 **ISSUE A**

DATE 11 JUN 2007



PIN 1 REFERENCE

0.10 C

0.10 С

0.05 С

0.05 C **TOP VIEW**

A1

SIDE VIEW

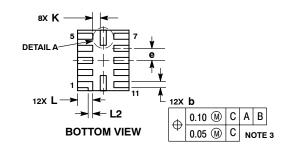
2X |

12X 🗀





DETAIL B OPTIONAL CONSTRUCTION

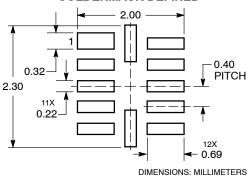


DETAIL B

SEATING PLANE

-A B

MOUNTING FOOTPRINT SOLDERMASK DEFINED



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM
- FROM TERMINAL TIP.

 MOLD FLASH ALLOWED ON TERMINALS

 ALONG EDGE OF PACKAGE. FLASH 0.03

 MAX ON BOTTOM SURFACE OF
- TERMINALS.
 DETAIL A SHOWS OPTIONAL
 CONSTRUCTION FOR TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A3	0.127	REF	
b	0.15	0.25	
D	1.70 BSC		
Е	2.00 BSC		
е	0.40	BSC	
K	0.20		
L	0.45	0.55	
L1	0.00	0.03	
12	0.15 RFF		

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

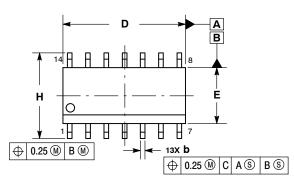
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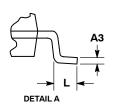
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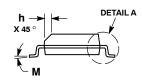


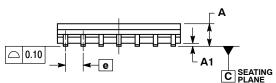
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016









0.25 0.50 0.010 0.019 0.40 1.25 0.016 0.049

NOTES:
1. DIMENSIONING AND TOLERANCING PER

5. MAXIMUM MOLD PROTRUSION 0.15 PER

INCHES

MIN MAX

0.050 BSC

0.25 0.004 0.010

0.25 0.008 0.010

0.49 0.014

8.75 0.337 3.80 4.00 0.150 0.157

0.068

0.019

MILLIMETERS

MIN MAX

1.27 BSC

0.19

8.55

SIDE

Α

A1 0.10

АЗ

b 0.35

D E

e H h

ASME Y14.5M, 1994.
CONTROLLING DIMENSION: MILLIMETERS. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.



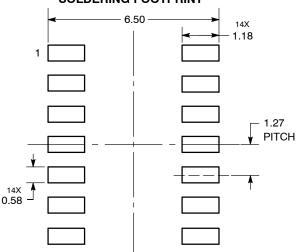
GENERIC

XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year = Work Week WW G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

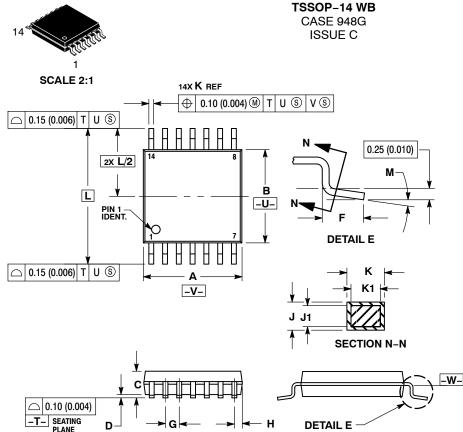
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

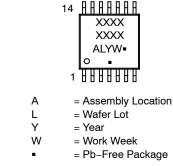
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY.
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	° o	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*



(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

—	7.06
1	
	
	U 0.65 PITCH
, <u> </u>	<u> </u>
14X	
0.36 14X 1.26	DIMENSIONS: MILLIMETERS

SOLDERING FOOTPRINT

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